



## 30V N-Channel Power MOSFET

TO-252 (DPAK)

#### Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

# 2 650

#### **Key Parameter Performance Parameter Value** Unit $V_{DS}$ 30 ٧ $V_{GS} = 10V$ 50 R<sub>DS(on)</sub> (max) $\, m\Omega$ $V_{GS} = 4.5V$ 80 4 $Q_g$ nC

#### **Application**

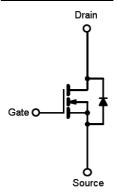
- Portable application
- DC to DC converter

#### **Ordering Information**

Part No.	Package	Packing
TSM500N03CP ROG	TO-252	2.5kpcs / 13" Reel

**Note:** "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds

### **Block Diagram**



N-Channel MOSFET

#### Absolute Maximum Ratings (T<sub>C</sub>=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current	T <sub>C</sub> =25°C		12.5	Α
	T <sub>C</sub> =100°C	l <sub>D</sub>	8	Α
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	40	Α
Power Dissipation @ T <sub>C</sub> =25°C		P <sub>D</sub>	12.5	W
Operating Junction Temperature		T <sub>J</sub>	150	°C
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit	
Thermal Resistance - Junction to Case	R <sub>eJC</sub>	10	2011	
Thermal Resistance - Junction to Ambient	R <sub>OJA</sub>	110	°C/W	

1/5 Version: A14



# 30V N-Channel Power MOSFET



**Electrical Specifications** (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						•
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	30			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 8A$	R <sub>DS(ON)</sub>		40	50	mΩ
	$V_{GS} = 4.5V, I_D = 8A$			65	80	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1	1.7	3	V
Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$				1	μA
	V <sub>DS</sub> = 24V, Tc = 150°C	I <sub>DSS</sub>			25	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Dynamic						
Total Gate Charge (Note 2,3)		$Q_g$		4		nC
Gate-Source Charge (Note 2,3)	$V_{DS} = 24V, I_{D} = 10A,$	$Q_gs$		1.6		
Gate-Drain Charge (Note 2,3)	$V_{GS} = 4.5V$	$Q_gd$		2.4		
Input Capacitance		C <sub>iss</sub>		270		pF
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ $V_{DS} = 1.0MHz$	C <sub>oss</sub>		70		
Reverse Transfer Capacitance		C <sub>rss</sub>		50		
Switching						
Turn-On Delay Time (Note 2,3)		t <sub>d(on)</sub>		7		
Turn-On Rise Time (Note 2,3)	$V_{DD} = 15V, I_D = 10A,$ $V_{GS} = 10V, R_{GEN} = 3.3\Omega$	t <sub>r</sub>		30		ns
Turn-Off Delay Time (Note 2,3)		t <sub>d(off)</sub>		10		
Turn-Off Fall Time (Note 2,3)		t <sub>f</sub>		3		
Source-Drain Diode Ratings and Ch	naracteristic					•
Diode-Source Forward Voltage	$V_{GS} = 0V$ , $I_S = 5A$	V <sub>SD</sub>			1.3	V
Reverse Recovery Time (Note 2)	V <sub>GS</sub> = 0V, I <sub>S</sub> = 10A	t <sub>rr</sub>		17		ns
Reverse Recovery Charge (Note 2)	$dI_F/dt = 100A/\mu s$	Q <sub>rr</sub>		10		nC

2/5

#### Note:

- 1. Pulse width limited by safe operating area
- 2. Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
- 3. Switching time is essentially independent of operating temperature.

Version: A14



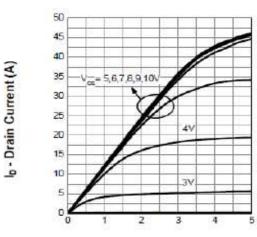
# 30V N-Channel Power MOSFET

Normalized On Resistance

lo - Drain Current (A)

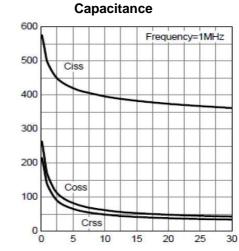
#### **Electrical Characteristics Curves**

#### **Output Characteristics**



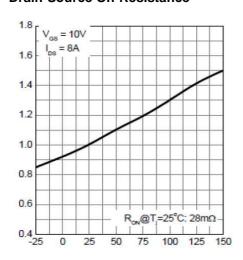
V<sub>DS</sub> - Drain-Source Voltage (V)

C - Capacitance (pF)



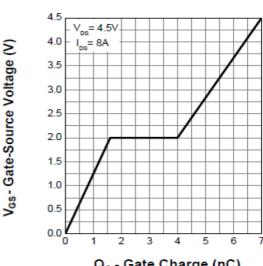
V<sub>DS</sub> - Drain-Source Voltage (V)

#### **Drain-Source On-Resistance**



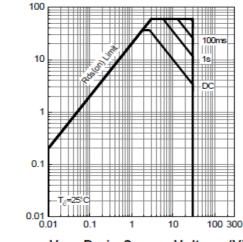
T<sub>j</sub> - Junction Temperature (°C)

Gate-Source Voltage vs. Gate Charge



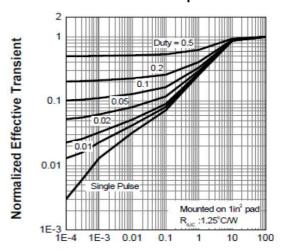
Q<sub>G</sub> - Gate Charge (nC)

#### Safe Operation Area



V<sub>DS</sub> - Drain-Source Voltage (V)

#### **Thermal Transient Impedance**



Square Wave Pulse Duration (sec)

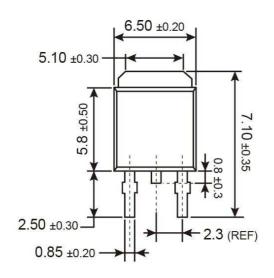
3/5 Version: A14

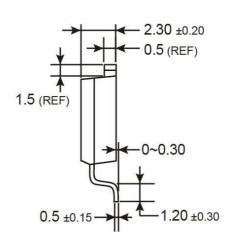


# 30V N-Channel Power MOSFET



# **TO-252 Mechanical Drawing**





Unit: Millimeters

# **Marking Diagram**



Y = Year Code

M = Month Code for Halogen Free Product
 (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep,
 X=Oct, Y=Nov, Z=Dec)

L = Lot Code

4/5 Version: A14



# TSM500N03 30V N-Channel Power MOSFET

#### **Notice**

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.

5/5 Version: A14